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STRUCTURE	Silicon Monolithic Integrated Circuit
PRODUCT NAME	γ -correction IC for TFT-LCD Panel
TYPE	B D 8 1 3 9 E F V
FEATURES	•Built-in 10ch γ-correction + Vcom outputs •I ² C Bus Interface Control (Built-in Auto Read)

⊖ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	LIMITS	UNIT
DVCC	7	V
VCC	20	V
REF	20	V
lo	50*1	mA
Tjmax	150	Ĵ
Pd	1600*2	mW
Topr	-30~+85	°.
Tstg	-55~+150	Ĵ
	DVCC VCC REF Io Tjmax Pd Topr	DVCC 7 VCC 20 REF 20 1o 50*1 Tjmax 150 Pd 1600*2 Topr -30~+85

*1 Do not however exceed Pd, ASO and Tjmax=150℃.

OPERATING CONDITION (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT
Power Supply Voltage 1	DVCC	2.3	4.0	V
Power Supply Voltage 2	VCC	6	18	V
REFIN Voltage	REF	6	18	V
Amplifier Drive Current	lo	_	40	mA
I ² C Bus Frequency	fCLK	_	400	KHZ
OSC Frequency	fosc	10	200	KHz

*The product described in this specification is a strategic product (and/or service) subject to COCOM regulations. It should not be exported without authorization from the appropriate government.

*This product is not designed for normal operation within a radio active environment.

*Status of this document

The Japanese version of this document is the formal specification.

A customer may use this translation version only for a reference to help reading the formal version.

If there are any differences in translation version of this document, formal version takes priority.

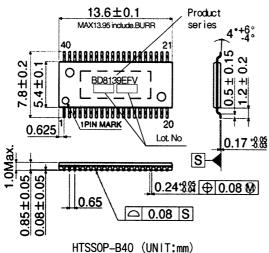
^{*2} Pd decreased at 12.8mV/°C for temperatures above Ta=25°C, mounted on 70×70×1.6mm Glass-epoxy PCB.

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OELECTRICAL CHARACTERISTICS (Unless otherwise specified VCC=15V, DVCC=3.3V, Ta=25°C)

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$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$		SYMBOL	LIMIT			CONDITIONS	
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$ \begin{array}{ c c c c c c c } \hline P_{1} & P_{2} $	(REFIN)					_	· · · · · · · · · · · · · · · · · · ·
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Sink Current	I REF	25	50	75	μA	REF=10V
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	[γ-CORRECTION AMP]					_	
Output Voltage HighVOHVCC-0.16VCC-0.1-VOutput Voltage LowVOL-0.10.16VIo=5mAIcoMMON AMPInput Bias CurrentIb-01 μ AVFB=6VDrive CurrentIo150300-mADAC=3V, OUTx=0VLoad Regulation ΔV -520mVIo=+10mA, OUTx=3VInput Voltage RangeVFB0-VDACVRo=100K Ω , Co=100pFOutput Voltage InighVOHVCC-0.16VCC-0.1-VIo=-5mAOutput Voltage LowVOL-0.10.16VIo=5mAOutput voltage LowVOL-0.10.16VIo=5mAOutput voltage LowVOL-0.10.16VIo=5mAOutput voltage LowVOL-0.10.16VIo=5mAI DACJ2LSBRange of OOA ~ 3F5 error with ideal straigtNon-Linear ErrorLE-2-2LSBRange of OOA ~ 3F5I Differential ErrorDLE-2-2LSBRange of OOA ~ 3F5I SOA output voltage LowVSDA0.4VIsDA=3,0mAInput leakage CurrentIct-1625uASDA output voltage LowVSDA0.4VISDA=3,0mAInput leakage CurrentILi-10-10 μ A0.4V~0.9DVCC <td></td> <td>lo</td> <td>150</td> <td></td> <td>-</td> <td>mA</td> <td>DAC=3V, OUTx=0V</td>		lo	150		-	mA	DAC=3V, OUTx=0V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	- · · · · · · · · · · · · · · · · · · ·	ΔV			20	mV	l_{0} =+10mA \sim -10mA, OUTx=6V
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$		VOH	VCC0.16	VCC-0.1	-	٧	lo=-5mA
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		VOL	-	0.1	0.16	V	lo=5mA
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$							
Load Regulation ΔV -520minInterview (Normation of the constraint o				•	.1	μA	VFB=6V
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$			150		-	mA	DAC=3V, OUTx=0V
Output Voltage highVOHVCC-0.16VCC-0.1-VIo=-5mAOutput voltage LowVOL-0.10.16VIo=5mAI DACIIO-BitIo=5mAResolution CodingRes-10-BitNon-Linear ErrorLE-2-2LSBRange of 00A \sim 3F5 error with ideal straighDifferential ErrorDLE-2-2LSBRange of 00A \sim 3F5[OSC]I-2LSBRange of 00A \sim 3F5[OSC]I-210-KHzInternal oscillator mode[CONTROL SIGNAL]I-1625UASink CurrentIctL-1625UASDA output voltage LowVSDA0.4VInput leakage CurrentILi-10-10 μA Input leakageVTH0.7-2.6VReset Timetrst-45- μ sCCT=1000pF[WHOLE DEVICE] μ sCCT=1000pF				5			$l_{o=+10mA} \sim -10mA$, $out_{x=3V}$
Output voltage LowVOL-0.10.16VIo=5mAI DAC]Resolution CodingRes-10-BitNon-Linear ErrorLE-2-2LSBRange of 00A \sim 3F5 error with ideal straighDifferential ErrorDLE-2-2LSBRange of 00A \sim 3F5[OSC]-2LSBerror with ideal amount of Increase in 1LSI[OSC]-210-KHzInternal oscillator mode[CONTROL SIGNAL]0.4VISDA=3.0mASink CurrentIctL-1625uAInput leakage CurrentILi-10-10 μ A0.4V~0.9DVCCThreshold VoltageVTH0.7-2.6VDVCC=3.3VReset Timetrst-45- μ sCCT=1000pF			v		VDAC	•	Ro=100KΩ, Co=100pF
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$			VCC0.16	VCC-0.1	-		lo=-5mA
Resolution CodingRes-10-BitNon-Linear ErrorLE-2-2LSBRange of 00A ~ 3F5 error with ideal straigDifferential ErrorDLE-2-2LSBRange of 00A ~ 3F5 error with ideal amount of Increase in 1LSI[OSC]		VOL		0.1	0.16	V	lo=5mA
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Differential ErrorDLE-2-22LSBRange of 00A \sim 3F5[OSC]	×			10	-	Bit	
Differential Endition DLE -2 - 2 LSB error with ideal amount of Increase in 1LSE [OSC]	Non-Linear Error	LE	-2	-	2	LSB	Range of OOA \sim 3F5 error with ideal straight
CONC error with ideal amount of Increase in 1LSt Frequency fosc - 210 - KHz Internal oscillator mode CONTROL SIGNAL	Differential Error	DLE	-2	-	2	LSB	
Frequencyfosc-210-KHzInternal oscillator mode[CONTROL SIGNAL]Sink CurrentIctL-1625uASDA output voltage LowVSDA0.4VISDA=3.0mAInput leakage CurrentILi-10-10 μ A0.4V~0.9DVCCThreshold VoltageVTH0.7-2.6VDVCC=3.3VReset Timetrst-45- μ sCCT=1000pF[WHOLE DEVICE]							error with ideal amount of Increase in 1LSB
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		6		010		1/11	
Sink CurrentIctL-1625UASDA output voltage LowVSDA0.4VISDA=3.0mAInput leakage CurrentILi-10-10 μ A0.4V~0.9DVCCThreshold VoltageVTH0.7-2.6VDVCC=3.3VReset Timetrst-45- μ sCCT=1000pF[WHOLE DEVICE]		TOSC	-	210	_	KHZ	Internal oscillator mode
SDA output voltage LowVSDA0.4VISDA=3.0mAInput leakage CurrentILi-10-10 μ A0.4V~0.9DVCCThreshold VoltageVTH0.7-2.6VDVCC=3.3VReset Timetrst-45- μ sCCT=1000pF[WHOLE DEVICE]		1.04	· · · · · ·	10			
$\begin{array}{c c c c c c c c c c c c c c c c c c c $			-	01			
Threshold Voltage VTH 0.7 - 2.6 V DVCC=3.3V Reset Time trst - 45 - µs CCT=1000pF [WHOLE DEVICE]			- 10	-			
Reset Time trst - 45 - μs CCT=1000pF [WHOLE DEVICE]							
(WHOLE DEVICE)							
		trst	-	45	-	μs	CCT=1000pF
MAAll outputs = 5V		<u> </u>		10			
				8	-	mA	All outputs = 5V

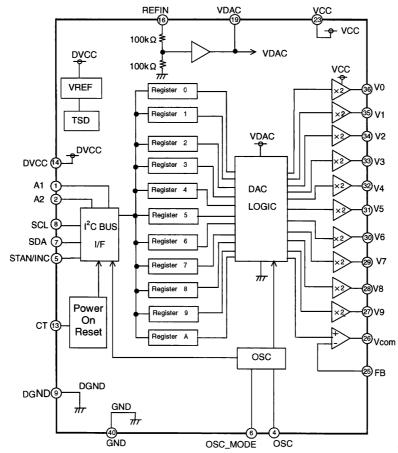
*This product is not designed for protection against radioactive rays.



OPHYSICAL DIMENSIONS . MARKING



OBLOCK DIAGRAM



%Refer to the Technical Note about the details of the application.

PIN No	PIN NAME	Function	PIN No	PIN NAME	Function
1	A1	Slave/Slave adress set① Autoread/word address set① for EEPROM	21	NC	_
2	A2	Slave/Slave adress set② Autoread/word address set② for EEPROM	22	NC	_
3	NC	_	23	VCC	POWER SUPPLY
4	0SC	SYNCHRONIZED CLOCK INPUT	24	NC	
5	STAN/INC	INPUT MODE SWITCH FOR 12C	25	FB	COM negative feedback INPUT
6	OSC_MODE	OSC MODE SWITCH (INTERNAL/EXTERNAL)	26	VCOM	COM OUTPUT
7	SDA	DATA SIGNAL INPUT FOR I ² C	27	V9	GAMMA 9 output
8	SCL	CLOCK SIGNAL INPUT FOR 12C	28	V8	GAMMA 8 output
9	DGND	GROUND	29	V7	GAMMA 7 output
10	DACGND	GROUND FOR DAC	30	V6	GAMMA 6 output
11	NC	_	31	V5	GAMMA 5 output
12	NC	—	32	V4	GAMMA 4 output
13	СТ	CAPACITOR CONNECTION FOR POWER ON RESET	33	V3	GAMMA 3 output
14	DVCC	DIGITAL POWER SUPPLY	34	V2	GAMMA 2 output
15	NC		35	V1	GAMMA 1 output
16	REFIN	DAC REFERENCE INPUT	36	V0	GAMMA 0 output
17	NC	_	37	NC	_
18	NC	_	38	NC	<u> </u>
19	VDAC	DAC VOLTAGE OUTPUT	39	NC	<u> </u>
20	NC	_	40	GND	GROUND

 $\bigcirc\,{\sf PIN}$ No, Pin Name, Function



• Operation Notes

1) Absolute maximum ratings

Use of the IC in excess of absolute maximum ratings such as the applied voltage or operating temperature range may result in IC damage. Assumptions should not be made regarding the state of the IC (short mode or open mode) when such damage is suffered. A physical safety measure such as a fuse should be implemented when use of the IC in a special mode where the absolute maximum ratings may be exceeded is anticipated.

2) GND potential

Ensure a minimum GND pin potential in all operating conditions.

3) Setting of heat

Use a setting of heat that allows for a sufficient margin in light of the power dissipation (Pd) in actual operating conditions. 4) Pin short and mistake fitting

Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Use of the IC in excess of absolute maximum ratings such as the applied voltage or operating temperature range may result in IC damage.

5) Actions in strong magnetic field

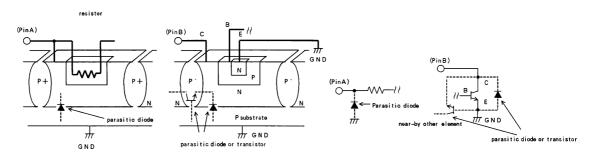
Use caution when using the IC in the presence of a strong electromagnetic field as doing so may cause the IC to malfunction. 6) Ground wiring patterns

When using both small signal and large current GND patterns, it is recommended to isolate the two ground patterns, placing a single ground point at the application's reference point so that the pattern wiring resistance and voltage variations caused by large currents do not cause variations in the small signal ground voltage. Be careful not to change the GND wiring patterns of any external components.

7) Regarding input pin of the IC

This monolithic IC contains P^+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements. For example, when a resistor and transistor are connected to pins. (see the chart below)

The formation of parasitic NPN transistors according to the relationships of different IC pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as by the application of voltages lower than the GND (P substrate) voltage to input and out



8) Thermal shutdown circuit (TSD)

This IC incorporates a built-in thermal shutdown circuit for the protection from thermal destruction. The IC should be used within the specified power dissipation range. However, in the event that the IC continues to be operated in excess of its power dissipation limits, the attendant rise in the chip's temperature Tj will trigger the thermal shutdown circuit to turn off all output power elements. The circuit will automatically reset once the chip's temperature Tj drops. Operation of the thermal shutdown circuit presumes that the IC's absolute maximum ratings have been exceeded. Application designs should never make use of the circuit.

9) Testing on application boards

When testing the IC on an application board, connecting a capacitor to a pin with low impedance subjects the IC to stress. Always discharge capacitors after each process or step. Ground the IC during assembly steps as an antistatic measure, and use similar caution when transporting or storing the IC. Always turn the IC's power supply off before connecting it to or removing it from a jig or fixture during the inspection process.

Notes

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As of 18th. April 2005